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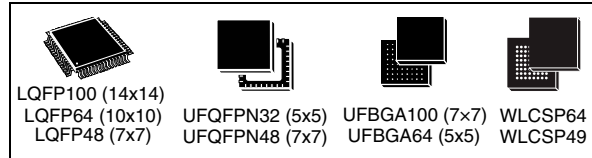


Ultra-low-power ARM[®] Cortex[®]-M4 32-bit MCU+FPU, 100DMIPS, up to 256KB Flash, 64KB SRAM, analog, audio

Datasheet - production data

Features

- Ultra-low-power with FlexPowerControl
 - 1.71 V to 3.6 V power supply
 - -40 °C to 85/105/125 °C temperature range
 - 200 nA in V_{BAT} mode: supply for RTC and 32x32-bit backup registers
 - 8 nA Shutdown mode (5 wakeup pins)
 - 28 nA Standby mode (5 wakeup pins)
 - 280 nA Standby mode with RTC
 - 1.0 µA Stop 2 mode, 1.28 µA Stop 2 with RTC
 - 84 µA/MHz run mode
 - Batch acquisition mode (BAM)
 - 4 µs wakeup from Stop mode
 - Brown out reset (BOR) in all modes except shutdown
 - Interconnect matrix
- Core: ARM[®] 32-bit Cortex[®]-M4 CPU with FPU, Adaptive real-time accelerator (ART Accelerator™) allowing 0-wait-state execution from Flash memory, frequency up to 80 MHz, MPU, 100DMIPS/1.25DMIPS/MHz (Dhrystone 2.1), and DSP instructions
- Performance Benchmark
 - 1.25 DMIPS/MHz (Dhrystone 2.1)
 - 273.55 Coremark[®] (3.42 Coremark/MHz @ 80 MHz)
- Energy Benchmark
 - 176.7 ULPBench[®] score
- Clock Sources
 - 4 to 48 MHz crystal oscillator
 - 32 kHz crystal oscillator for RTC (LSE)
 - Internal 16 MHz factory-trimmed RC (±1%)
 - Internal low-power 32 kHz RC (±5%)
 - Internal multispeed 100 kHz to 48 MHz oscillator, auto-trimmed by LSE (better than ±0.25 % accuracy)
 - Internal 48 MHz with clock recovery



- 2 PLLs for system clock, audio, ADC
- RTC with HW calendar, alarms and calibration
- Up to 21 capacitive sensing channels: support touchkey, linear and rotary touch sensors
- 11x timers: 1x 16-bit advanced motor-control, 1x 32-bit and 2x 16-bit general purpose, 2x 16-bit basic, 2x low-power 16-bit timers (available in Stop mode), 2x watchdogs, SysTick timer
- Up to 83 fast I/Os, most 5 V-tolerant
- Memories
 - Up to 256 KB single bank Flash, proprietary code readout protection
 - 64 KB of SRAM including 16 KB with hardware parity check
 - Quad SPI memory interface
- Rich analog peripherals (independent supply)
 - 1x 12-bit ADC 5 Msps, up to 16-bit with hardware oversampling, 200 µA/Msps
 - 2x 12-bit DAC, low-power sample and hold
 - 1x operational amplifier with built-in PGA
 - 2x ultra-low-power comparators
- 15x communication interfaces
 - 1x SAI (serial audio interface)
 - 3x I2C FM+(1 Mbit/s), SMBus/PMBus
 - 4x USARTs (ISO 7816, LIN, IrDA, modem)
 - 3x SPIs (4x SPIs with the Quad SPI)
 - CAN (2.0B Active) and SDMMC interface
 - SWPMI single wire protocol master I/F
 - IRTIM (Infrared interface)
- 14-channel DMA controller
- True random number generator
- CRC calculation unit, 96-bit unique ID

- Development support: serial wire debug (SWD), JTAG, Embedded Trace Macrocell™

Table 1. Device summary

Reference	Part numbers
STM32L431xx	STM32L431CC, STM32L431KC, STM32L431RC, STM32L431VC, STM32L431CB, STM32L431KB, STM32L431RB

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L431xx microcontrollers.

This document should be read in conjunction with the STM32L4x1 reference manual (RM0392). The reference manual is available from the STMicroelectronics website www.st.com.

For information on the ARM® Cortex®-M4 core, please refer to the Cortex®-M4 Technical Reference Manual, available from the www.arm.com website.



2 Description

The STM32L431xx devices are the ultra-low-power microcontrollers based on the high-performance ARM[®] Cortex[®]-M4 32-bit RISC core operating at a frequency of up to 80 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32L431xx devices embed high-speed memories (Flash memory up to 256 Kbyte, 64 Kbyte of SRAM), a Quad SPI flash memories interface (available on all packages) and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses and a 32-bit multi-AHB bus matrix.

The STM32L431xx devices embed several protection mechanisms for embedded Flash memory and SRAM: readout protection, write protection, proprietary code readout protection and Firewall.

The devices offer a fast 12-bit ADC (5 Msps), two comparators, one operational amplifier, two DAC channels, an internal voltage reference buffer, a low-power RTC, one general-purpose 32-bit timer, one 16-bit PWM timer dedicated to motor control, four general-purpose 16-bit timers, and two 16-bit low-power timers.

In addition, up to 21 capacitive sensing channels are available.

They also feature standard and advanced communication interfaces.

- Three I2Cs
- Three SPIs
- Three USARTs and one Low-Power UART.
- One SAI (Serial Audio Interfaces)
- One SDMMC
- One CAN
- One SWPMI (Single Wire Protocol Master Interface)

The STM32L431xx operates in the -40 to +85 °C (+105 °C junction), -40 to +105 °C (+125 °C junction) and -40 to +125 °C (+130 °C junction) temperature ranges from a 1.71 to 3.6 V power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

Some independent power supplies are supported: analog independent supply input for ADC, DAC, OPAMPs and comparators. A VBAT input allows to backup the RTC and backup registers.

The STM32L431xx family offers nine packages from 32 to 100-pin packages.

Table 2. STM32L431xx family device features and peripheral counts

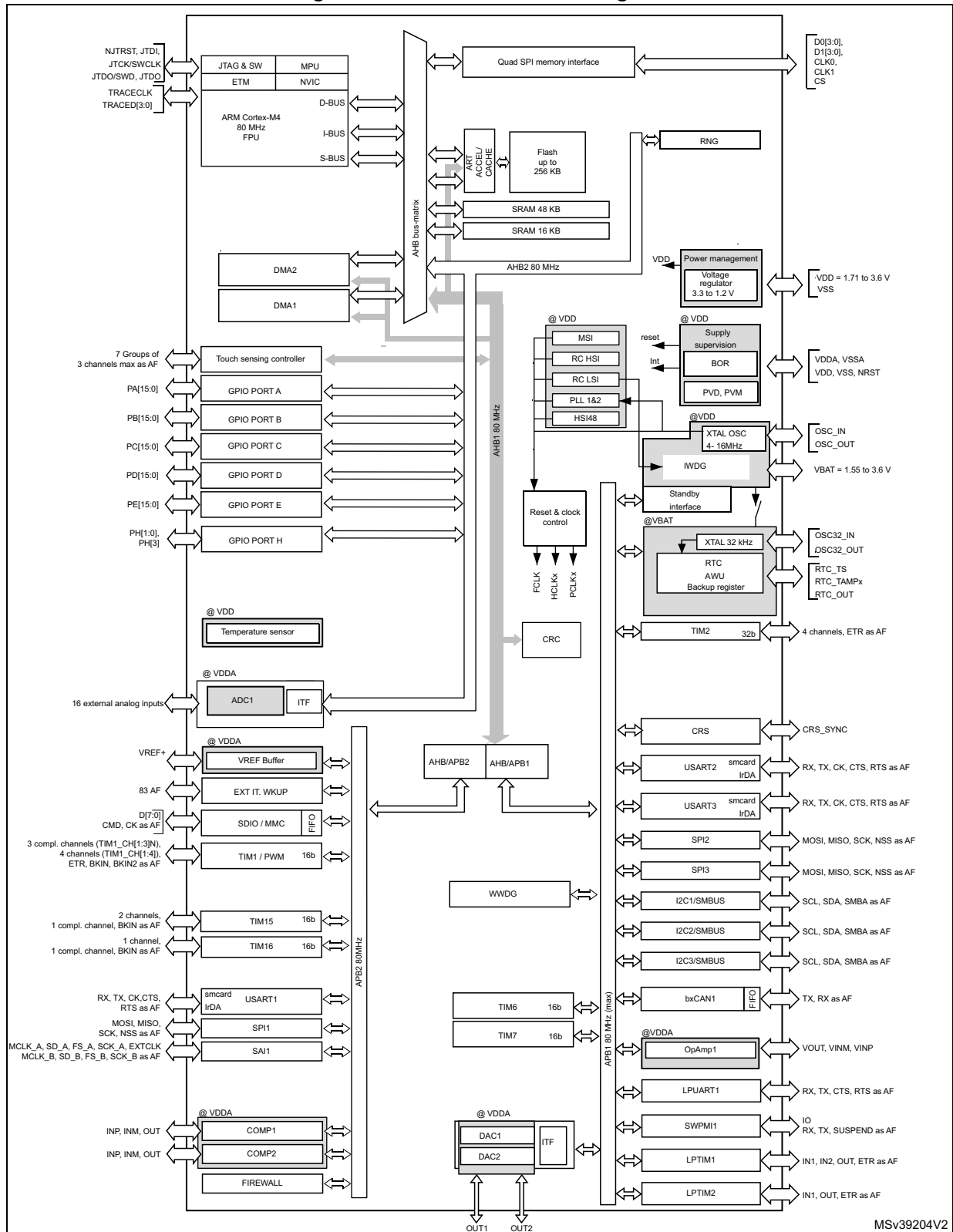
Peripheral	STM32L431Vx	STM32L431Rx		STM32L431Cx		STM32L431Kx	
Flash memory	256KB	128KB	256KB	128KB	256KB	128KB	256KB
SRAM	64KB						
Quad SPI	Yes						

Table 2. STM32L431xx family device features and peripheral counts (continued)

Peripheral		STM32L431Vx	STM32L431Rx	STM32L431Cx	STM32L431Kx	
Timers	Advanced control	1 (16-bit)				
	General purpose	2 (16-bit) 1 (32-bit)				
	Basic	2 (16-bit)				
	Low -power	2 (16-bit)				
	SysTick timer	1				
	Watchdog timers (independent, window)	2				
Comm. interfaces	SPI	3			2	
	I ² C	3			2	
	USART LPUART	3 1			2 1	
	SAI	1				
	CAN	1				
	SDMMC	Yes		No		
	SWPMI	Yes				
RTC	Yes					
Tamper pins	3	2	2	1		
Random generator	Yes					
GPIOs	83	52	38 or 39 ⁽¹⁾	26		
Wakeup pins	5	4	3	2		
Capacitive sensing Number of channels	21	12	6	3		
12-bit ADCs	1	1	1	1		
Number of channels	16	16	10	10		
12-bit DAC channels	2					
Internal voltage reference buffer	Yes	No				
Analog comparator	2					
Operational amplifiers	1					
Max. CPU frequency	80 MHz					
Operating voltage	1.71 to 3.6 V					
Operating temperature	Ambient operating temperature: -40 to 85 °C / -40 to 105 °C / -40 to 125 °C Junction temperature: -40 to 105 °C / -40 to 125 °C / -40 to 130 °C					
Packages	LQFP100 UFBGA100	WLCSP64 LQFP64 UFBGA64	WLCSP49 LQFP48 UFQFPN48	UFQFPN32		

1. For WLCSP49 package.

Figure 1. STM32L431xx block diagram



Note: AF: alternate function on I/O pins.



3 Functional overview

3.1 ARM[®] Cortex[®]-M4 core with FPU

The ARM[®] Cortex[®]-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM[®] Cortex[®]-M4 with FPU 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded ARM core, the STM32L431xx family is compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the STM32L431xx family devices.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM[®] Cortex[®]-M4 processors. It balances the inherent performance advantage of the ARM[®] Cortex[®]-M4 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor near 100 DMIPS performance at 80MHz, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 64-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 80 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.4 Embedded Flash memory

STM32L431xx devices feature up to 256 Kbyte of embedded Flash memory available for storing programs and data in single bank architecture. The Flash memory contains 128 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
 - Level 0: no readout protection
 - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
 - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A ⁽¹⁾	No	No	N/A ⁽¹⁾
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes ⁽¹⁾	No	No	No ⁽¹⁾
	2	Yes	Yes	Yes	N/A	N/A	N/A

1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. The PCROP area granularity is 64-bit wide. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

The whole non-volatile memory embeds the error correction code (ECC) feature supporting:

- single error detection and correction
- double error detection.
- The address of the ECC fail can be read in the ECC register

3.5 Embedded SRAM

STM32L431xx devices feature 64 Kbyte of embedded SRAM. This SRAM is split into two blocks:

- 48 Kbyte mapped at address 0x2000 0000 (SRAM1)
- 16 Kbyte located at address 0x1000 0000 with hardware parity check (SRAM2).

This memory is also mapped at address 0x2000 C000, offering a contiguous address space with the SRAM1 (16 Kbyte aliased by bit band)

This block is accessed through the ICode/DCode buses for maximum performance. These 16 Kbyte SRAM can also be retained in Standby mode.

The SRAM2 can be write-protected with 1 Kbyte granularity.

The memory can be accessed in read/write at CPU clock speed with 0 wait states.

3.6 Firewall

The device embeds a Firewall which protects code sensitive and secure data from any access performed by a code executed outside of the protected areas.

Each illegal access generates a reset which kills immediately the detected intrusion.

The Firewall main features are the following:

- Three segments can be protected and defined thanks to the Firewall registers:
 - Code segment (located in Flash or SRAM1 if defined as executable protected area)
 - Non-volatile data segment (located in Flash)
 - Volatile data segment (located in SRAM1)
- The start address and the length of each segments are configurable:
 - code segment: up to 1024 Kbyte with granularity of 256 bytes
 - Non-volatile data segment: up to 1024 Kbyte with granularity of 256 bytes
 - Volatile data segment: up to 48 Kbyte with a granularity of 64 bytes
- Specific mechanism implemented to open the Firewall to get access to the protected areas (call gate entry sequence)
- Volatile data segment can be shared or not with the non-protected code
- Volatile data segment can be executed or not depending on the Firewall configuration

The Flash readout protection must be set to level 2 in order to reach the expected level of protection.

3.7 Boot modes

At startup, BOOT0 pin or nSWBOOT0 option bit, and BOOT1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

BOOT0 value may come from the PH3-BOOT0 pin or from an option bit depending on the value of a user option bit to free the GPIO pad if needed.

A Flash empty check mechanism is implemented to force the boot from system flash if the first flash memory location is not programmed and if the boot selection is configured to boot from main flash.

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART, I2C, SPI and CAN in Device mode through DFU (device firmware upgrade).

3.8 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.9 Power supply management

3.9.1 Power supply schemes

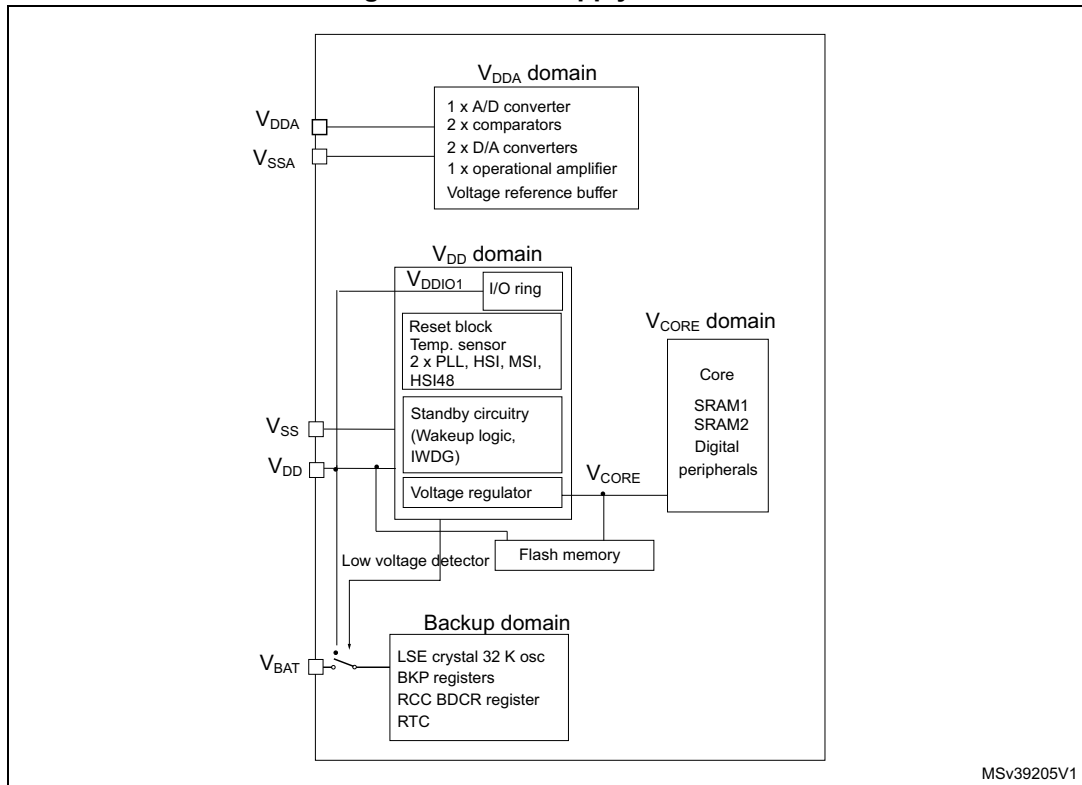
- $V_{DD} = 1.71$ to 3.6 V: external power supply for I/Os (V_{DDIO1}), the internal regulator and the system analog such as reset, power management and internal clocks. It is provided externally through V_{DD} pins.
- $V_{DDA} = 1.62$ V (ADCs/COMP) / 1.8 (DACs/OPAMP) to 3.6 V: external analog power supply for ADCs, DACs, OPAMP, Comparators and Voltage reference buffer. The V_{DDA} voltage level is independent from the V_{DD} voltage.
- $V_{BAT} = 1.55$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Note: When the functions supplied by V_{DDA} are not used, this supply should preferably be shorted to V_{DD} .

Note: If these supplies are tied to ground, the I/Os supplied by these power supplies are not 5 V tolerant (refer to [Table 18: Voltage characteristics](#)).

Note: V_{DDIOx} is the I/Os general purpose digital functions supply. V_{DDIOx} represents V_{DDIO1} , with $V_{DDIO1} = V_{DD}$.

Figure 2. Power supply overview



MSv39205V1

3.9.2 Power supply supervisor

The device has an integrated ultra-low-power brown-out reset (BOR) active in all modes except Shutdown and ensuring proper operation after power-on and during power down. The device remains in reset mode when the monitored supply voltage V_{DD} is below a specified threshold, without the need for an external reset circuit.

The lowest BOR level is 1.71V at power on, and other higher thresholds can be selected through option bytes. The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the VPVD threshold. An interrupt can be generated when V_{DD} drops below the VPVD threshold and/or when V_{DD} is higher than the VPVD threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

In addition, the devices embed a Peripheral Voltage Monitor which compares the independent supply voltage V_{DDA} with a fixed threshold in order to ensure that the peripheral is in its functional supply range.

3.9.3 Voltage regulator

Two embedded linear voltage regulators supply most of the digital circuitries: the main regulator (MR) and the low-power regulator (LPR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-Power Run, Low-Power Sleep, Stop 1 and Stop 2 modes. It is also used to supply the 16 Kbyte SRAM2 in Standby with RAM2 retention.
- Both regulators are in power-down in Standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The ultralow-power STM32L431xx supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the Main Regulator that supplies the logic (VCORE) can be adjusted according to the system's maximum operating frequency.

There are two power consumption ranges:

- Range 1 with the CPU running at up to 80 MHz.
- Range 2 with a maximum CPU frequency of 26 MHz. All peripheral clocks are also limited to 26 MHz.

The VCORE can be supplied by the low-power regulator, the main regulator being switched off. The system is then in Low-power run mode.

- Low-power run mode with the CPU running at up to 2 MHz. Peripherals with independent clock can be clocked by HSI16.

3.9.4 Low-power modes

The ultra-low-power STM32L431xx supports seven low-power modes to achieve the best compromise between low-power consumption, short startup time, available peripherals and available wakeup sources:

By default, the microcontroller is in Run mode after a system or a power Reset. It is up to the user to select one of the low-power modes described below:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
- **Low-power run mode**
This mode is achieved with VCORE supplied by the low-power regulator to minimize the regulator's operating current. The code can be executed from SRAM or from Flash, and the CPU frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16.
- **Low-power sleep mode**
This mode is entered from the low-power run mode. Only the CPU clock is stopped. When wakeup is triggered by an event or an interrupt, the system reverts to the low-power run mode.
- **Stop 0, Stop 1 and Stop 2 modes**
Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the VCORE domain are stopped, the PLL, the MSI

RC, the HSI16 RC and the HSE crystal oscillators are disabled. The LSE or LSI is still running.

The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

Some peripherals with wakeup capability can enable the HSI16 RC during Stop mode to detect their wakeup condition.

Three Stop modes are available: Stop 0, Stop 1 and Stop 2 modes. In Stop 2 mode, most of the VCORE domain is put in a lower leakage mode.

Stop 1 offers the largest number of active peripherals and wakeup sources, a smaller wakeup time but a higher consumption than Stop 2. In Stop 0 mode, the main regulator remains ON, allowing a very fast wakeup time but with much higher consumption.

The system clock when exiting from Stop 0, Stop1 or Stop2 modes can be either MSI up to 48 MHz or HSI16, depending on software configuration.

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption with BOR. The internal regulator is switched off so that the VCORE domain is powered off. The PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are also switched off.

The RTC can remain active (Standby mode with RTC, Standby mode without RTC).

The brown-out reset (BOR) always remains active in Standby mode.

The state of each I/O during standby mode can be selected by software: I/O with internal pull-up, internal pull-down or floating.

After entering Standby mode, SRAM1 and register contents are lost except for registers in the Backup domain and Standby circuitry. Optionally, SRAM2 can be retained in Standby mode, supplied by the low-power Regulator (Standby with RAM2 retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

The system clock after wakeup is MSI up to 8 MHz.

- **Shutdown mode**

The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the VCORE domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

The system clock after wakeup is MSI at 4 MHz.

Table 4. Functionalities depending on the working mode⁽¹⁾

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
CPU	Y	-	Y	-	-	-	-	-	-	-	-	-	-
Flash memory (up to 256 KB)	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	-	-	-	-	-	-	-	-	-
SRAM1 (48 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	-	-	-	-	-
SRAM2 (16 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	O ⁽⁴⁾	-	-	-	-
Quad SPI	O	O	O	O	-	-	-	-	-	-	-	-	-
Backup Registers	Y	Y	Y	Y	Y	-	Y	-	Y	-	Y	-	Y
Brown-out reset (BOR)	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	-	-	-
Programmable Voltage Detector (PVD)	O	O	O	O	O	O	O	O	-	-	-	-	-
Peripheral Voltage Monitor (PVMx; x=1,3,4)	O	O	O	O	O	O	O	O	-	-	-	-	-
DMA	O	O	O	O	-	-	-	-	-	-	-	-	-
High Speed Internal (HSI16)	O	O	O	O	(5)	-	(5)	-	-	-	-	-	-
Oscillator RC48	O	O	-	-	-	-	-	-	-	-	-	-	-
High Speed External (HSE)	O	O	O	O	-	-	-	-	-	-	-	-	-
Low Speed Internal (LSI)	O	O	O	O	O	-	O	-	O	-	-	-	-
Low Speed External (LSE)	O	O	O	O	O	-	O	-	O	-	O	-	O
Multi-Speed Internal (MSI)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System (CSS)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System on LSE	O	O	O	O	O	O	O	O	O	O	-	-	-
RTC / Auto wakeup	O	O	O	O	O	O	O	O	O	O	O	O	O
Number of RTC Tamper pins	3	3	3	3	3	O	3	O	3	O	3	O	3
USARTx (x=1,2,3)	O	O	O	O	O ⁽⁶⁾	O ⁽⁶⁾	-	-	-	-	-	-	-



Table 4. Functionalities depending on the working mode⁽¹⁾ (continued)

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
Low-power UART (LPUART)	○	○	○	○	○ ⁽⁶⁾	○ ⁽⁶⁾	○ ⁽⁶⁾	○ ⁽⁶⁾	-	-	-	-	-
I2Cx (x=1,2)	○	○	○	○	○ ⁽⁷⁾	○ ⁽⁷⁾	-	-	-	-	-	-	-
I2C3	○	○	○	○	○ ⁽⁷⁾	○ ⁽⁷⁾	○ ⁽⁷⁾	○ ⁽⁷⁾	-	-	-	-	-
SPIx (x=1,2,3)	○	○	○	○	-	-	-	-	-	-	-	-	-
CAN	○	○	○	○	-	-	-	-	-	-	-	-	-
SDMMC1	○	○	○	○	-	-	-	-	-	-	-	-	-
SWPMI1	○	○	○	○	-	○	-	-	-	-	-	-	-
SAIx (x=1)	○	○	○	○	-	-	-	-	-	-	-	-	-
ADCx (x=1)	○	○	○	○	-	-	-	-	-	-	-	-	-
DACx (x=1,2)	○	○	○	○	○	-	-	-	-	-	-	-	-
VREFBUF	○	○	○	○	○	-	-	-	-	-	-	-	-
OPAMPx (x=1)	○	○	○	○	○	-	-	-	-	-	-	-	-
COMPx (x=1,2)	○	○	○	○	○	○	○	○	-	-	-	-	-
Temperature sensor	○	○	○	○	-	-	-	-	-	-	-	-	-
Timers (TIMx)	○	○	○	○	-	-	-	-	-	-	-	-	-
Low-power timer 1 (LPTIM1)	○	○	○	○	○	○	○	○	-	-	-	-	-
Low-power timer 2 (LPTIM2)	○	○	○	○	○	○	-	-	-	-	-	-	-
Independent watchdog (IWDG)	○	○	○	○	○	○	○	○	○	○	-	-	-
Window watchdog (WWDG)	○	○	○	○	-	-	-	-	-	-	-	-	-
SysTick timer	○	○	○	○	-	-	-	-	-	-	-	-	-
Touch sensing controller (TSC)	○	○	○	○	-	-	-	-	-	-	-	-	-
Random number generator (RNG)	○ ⁽⁸⁾	○ ⁽⁸⁾	-	-	-	-	-	-	-	-	-	-	-

Table 4. Functionalities depending on the working mode⁽¹⁾ (continued)

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
CRC calculation unit	O	O	O	O	-	-	-	-	-	-	-	-	-
GPIOs	O	O	O	O	O	O	O	O	⁽⁹⁾ 5 pins ₍₁₀₎	⁽¹¹⁾ 5 pins ₍₁₀₎	-	-	-

- Legend: Y = Yes (Enable). O = Optional (Disable by default. Can be enabled by software). - = Not available.
- The Flash can be configured in power-down mode. By default, it is not in power-down mode.
- The SRAM clock can be gated on or off.
- SRAM2 content is preserved when the bit RRS is set in PWR_CR3 register.
- Some peripherals with wakeup from Stop capability can request HSI16 to be enabled. In this case, HSI16 is woken up by the peripheral, and only feeds the peripheral which requested it. HSI16 is automatically put off when the peripheral does not need it anymore.
- UART and LPUART reception is functional in Stop mode, and generates a wakeup interrupt on Start, address match or received frame event.
- I2C address detection is functional in Stop mode, and generates a wakeup interrupt in case of address match.
- Voltage scaling Range 1 only.
- I/Os can be configured with internal pull-up, pull-down or floating in Standby mode.
- The I/Os with wakeup from Standby/Shutdown capability are: PA0, PC13, PE6, PA2, PC5.
- I/Os can be configured with internal pull-up, pull-down or floating in Shutdown mode but the configuration is lost when exiting the Shutdown mode.

3.9.5 Reset mode

In order to improve the consumption under reset, the I/Os state under and after reset is “analog state” (the I/O schmitt trigger is disable). In addition, the internal reset pull-up is deactivated when the reset source is internal.

3.9.6 VBAT operation

The VBAT pin allows to power the device VBAT domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present. The VBAT pin supplies the RTC with LSE and the backup registers. Three anti-tamper detection pins are available in VBAT mode.

VBAT operation is automatically activated when V_{DD} is not present.

An internal VBAT battery charging circuit is embedded and can be activated when V_{DD} is present.

Note: When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from VBAT operation.